[0010] Based on the foregoing discovery, the present invention provides the following:

1) A sputtering target containing, as metal components, 0.5 to 45 mol% of Cr and remainder being Co, and containing, as non-metal components, two or more types of oxides including Ti oxide, wherein a structure of the sputtering target is configured from regions where oxides including at least Ti oxide are dispersed in Co (non-Cr-based regions), and a region where oxides other than Ti oxide are dispersed in Cr or Co-Cr (Cr-based region), and the non-Cr-based regions are scattered in the Cr-based region.

2) A sputtering target containing, as metal components, 0.5 to 30 mol% of Cr, 0.5 to 30 mol% of Pt, and remainder being Co, and containing, as non-metal components, two or more types of oxides including Ti oxide, wherein a structure of the sputtering target is configured from regions where oxides including at least Ti oxide are dispersed in Co or Co-Pt (non-Cr-based regions), and a region where oxides other than Ti oxide are dispersed in one or more types of phases of Co-Cr, Cr-Pt, and Co-Cr-Pt (Cr-based region), and the non-Cr-based regions are scattered in the Cr-based region.

3) The sputtering target according to 1) or 2) above, wherein the two or more types of oxides (excluding Ti oxide) are oxides of one or more types of elements selected from B, Mg, Al, Si, Cr, Zr, Nb, and Ta.

4) The sputtering target according to any one of 1) to 3) above, wherein a content of the oxides in the sputtering target is, based on a volume ratio, 20% or more and less than 50%.

5) The sputtering target according to any one of 1) to 4) above, wherein the sputtering target additionally contains, as metal components, one or more types of elements selected from B, Cu, Mo, Ru, Ta, and W.

[0011] 6) A method of producing a sputtering target comprising a step of mixing a metal powder and an oxide powder including Ti oxide and pressing and sintering a resulting mixed powder A in a vacuum or an inert gas atmosphere to produce a sintered compact A, and pulverizing and sieving the sintered compact A to produce a sintered compact powder A corresponding to the non-Cr-based regions, a step of mixing a metal powder and oxide powders other than Ti oxide to produce a mixed powder B corresponding to the Cr-based region, and a step of mixing the sintered compact powder A and the mixed powder B, and thereafter pressing and sintering a

CLAIMS

1. ~~(Amended)~~ A sputtering target containing, as metal components, 0.5 to 45 mol% of Cr and remainder being Co, and containing, as non-metal components, two or more types of oxides including Ti oxide, wherein a structure of the sputtering target is configured from regions where oxides including at least Ti oxide are dispersed in Co (non-Cr-based regions: note that the term "non-Cr-based regions" refers to "regions that do not include metal Cr"; hereinafter the same), and a region where oxides other than Ti oxide are dispersed in Cr or Co-Cr (Cr-based region), and the non-Cr-based regions are scattered in the Cr-based region.

2. A sputtering target containing, as metal components, 0.5 to 30 mol% of Cr, 0.5 to 30 mol% of Pt, and remainder being Co, and containing, as non-metal components, two or more types of oxides including Ti oxide, wherein a structure of the sputtering target is configured from regions where oxides including at least Ti oxide are dispersed in Co or Co-Pt (non-Cr-based regions), and a region where oxides other than Ti oxide are dispersed in one or more types of phases of Co-Cr, Cr-Pt, and Co-Cr-Pt (Cr-based region), and the non-Cr-based regions are scattered in the Cr-based region.

3. The sputtering target according to claim 1 or claim 2, wherein the two or more types of oxides (excluding Ti oxide) are oxides of one or more types of elements selected from B, Mg, Al, Si, Cr, Zr, Nb, and Ta.

4. The sputtering target according to any one of claims 1 to 3, wherein a content of the oxides in the sputtering target is, based on a volume ratio, 20% or more and less than 50%.

5. The sputtering target according to any one of claims 1 to 4, wherein the sputtering target additionally contains, as metal components, one or more types of elements selected from B, Cu, Mo, Ru, Ta, and W.

6. ~~(Amended)~~ A method of producing a sputtering target comprising a step of mixing a metal powder and an oxide powder including Ti oxide and pressing and sintering a resulting mixed powder A in a vacuum or an inert gas atmosphere to produce a sintered compact A, and pulverizing and sieving the sintered compact A to produce a sintered compact powder A corresponding to non-Cr-based regions, a step of mixing a metal powder and oxide powders other than Ti oxide to produce a mixed powder B corresponding to a Cr-based region, and a step of mixing the sintered compact powder A and the mixed powder B, and thereafter pressing and sintering a resulting

mixed powder in a vacuum or an inert gas atmosphere to produce a secondary sintered compact to be used as a target material.

7. The method of producing a sputtering target according to claim 6, wherein a grain size of the sintered compact powder A is 20 to 200 μm.